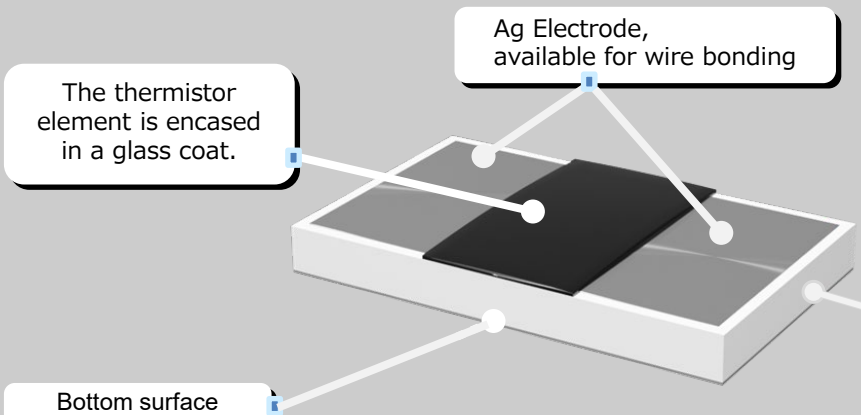
TATEYAMA

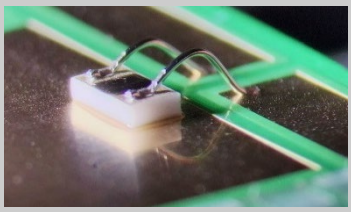
量産 NEW

200°C Wire-Bondable Chip Thermistor for SiC/GaN Modules

Engineered for High-Temperature Power Module Applications

Crafted through ingenious material design, precision mixing processes, and safeguarded by patent protection.





Wire-Bonding

Accordance with RoHS

Features

- Optimized for high temperature sensing, control, and compensation.
- Wide temperature ranges from -50℃ to +200℃ are ideal for SiC and GaN.
- The top surface has two electrodes Ag perfectly suitable for wire bonding.
- The bottom surface is metallized with Ag for sintering.
- Empowered by an Alumina base and Glass coating, ensuring high mechanical strength.
- Unparalleled thermal responsiveness due to its compact cubic volume and exceptional heat capacity.
- Thermal Response: Featuring minimal thermal capacity, yet heightened sensor sensitivity.
- AEC-Q200 compliant product.
- Formic acid reflow compliant product.

Application

- SiC/GaN Power modules
- Inverter for EV and HEV Vehicles
- IGBT(Insulated Gate Bipolar Transistor)
- MOSFET(Metal-Oxide-Semiconductor Field-Effect Transistor)
- DC-DC Converter
- Temperature management of the On-Board Charger
- Temperature compensation of semiconductors
- Automotive ABS control circuit

The product characteristics can be customized according to customer requirements. Please feel free to contact us.

Specification data

Chip size (mm)	Operating temperature	Resistance at 25℃	Resistance tolerance	B Constant (25℃/85℃)	B constant tolerance	Rated power at 25℃	Maximum permissible power	Thermal dissipation constant (in air)
2.0× 1.2mm (0.8× 0.5inch)	-50℃ ～ +200°C	1k ～ 500kΩ	±1%,±2%, ±3%,±5%, ±10%	3375～4500K	±1%,±2%, ±3%,±5%,	130mW	5mW	δ≦1.5mW/℃

※ Please contact us for in case of any other specifications.